AZ Power Inc. Providing A to Z Power Solutions

S2D120V012A SiC Schottky Diode

Features:

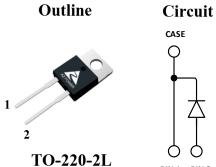
- 1200V Schottky Diode •
- Zero Reverse Recovery Current .
- High Frequency Operation •
- Positive Temperature Coefficient •
- Temperature independent • Switching

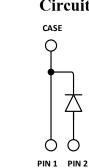
Applications:

- Switch Mode Power Supply •
- Booster diodes in PFC, DC/DC •
- AC/DC converters

- Unipolar Rectifier •
- Minimal switching loss .
- Higher Efficiency •
- Low cooling requirement •

Symbol	Value	Unit		
V _{RRM}	1200	V		
$I_F \ (Tc = 151^{\circ}C)$	12	А		
Qc	57	nC		





Symbol	Parameter	Value	Unit	Test Conditions
VR	DC Peak Reverse Voltage	1200	v	$T_J = 25^{\circ}C$
V _{RRM}	Repetitive Peak Reverse	1200	v	$T_J = 25^{\circ}C$
V _{RSM}	Surge Peak Reverse Voltage	1300	v	$T_J = 25^{\circ}C$
IF	Continuous Forward Current	36 19 12	А	$T_{\rm C} = 25^{\circ}{\rm C}$ $T_{\rm C} = 125^{\circ}{\rm C}$ $T_{\rm C} = 151^{\circ}{\rm C}$
I _{FRM}	Repetitive Peak Forward Surge Current	86 64	А	$T_C = 25^{\circ}C$, $T_P = 10ms$, Half Sine Wave $Tc = 125^{\circ}C$, $T_P = 10ms$, Half Sine Wave
I _{FSM}	Non-Repetitive Peak Forward Surge Current	114 97	А	$T_{\rm C} = 25^{\circ}$ C, $T_{\rm P} = 10$ ms, Half Sine Wave Tc = 125°C, $T_{\rm P} = 10$ ms, Half Sine Wave
PD	Power Dissipation	187 62.5	W	$T_{\rm C} = 25^{\circ}{\rm C}$ $T_{\rm C} = 125^{\circ}{\rm C}$
T _{J,max}	Operating Junction Temperature	175	°C	
Tstg	Storage Temperature Range	-55 to 175	°C	

Maximum Ratings

S2D120V012A, Rev. 1.1

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Thermal characteristics

Symbol	Parameter	Min.	Тур.	Max.	Unit
R _{thJC}	Thermal resistance		0.8		°C/W

Electrical Characteristics

Symbol	Parameter	Value		Unit	Test Conditions	
		Min.	Тур.	Max.	Unit	Test Conditions
V _{DC}	DC Blocking Voltage	1200			V	$I_R = 100 \mu A, T_J = 25^{\circ}C$
V _F	Forward Voltage		1.6	1.9	v	$I_F = 12A, T_J = 25^{\circ}C$
v F	V _F Forward Voltage 2.4	2.7	v	$I_F = 12A, T_J = 175^{\circ}C$		
I.	Reverse Current	1 50 u	A	$V_{R} = 1200V, T_{J} = 25^{\circ}C$		
IR	I _R Reverse Current		15	160	μA	$V_R = 1200V, T_J = 175^{\circ}C$
О т	Total Compatitive Change	57	57		nC	$I_{\rm F} = 12$ A, dI/dt = 300A/µs
Qc	Total Capacitive Charge		57			$T_J = 25^{\circ}C, V_R = 800V$
			628			$V_{R} = 1V, T_{J} = 25^{\circ}C, f = 1 \text{ MHz}$
С	Total Capacitance		56		pF	V_R =400V, T_J =25°C, f=1 MHz
			51			V_R =800V, T_J =25°C, f=1 MHz

Typical Performance

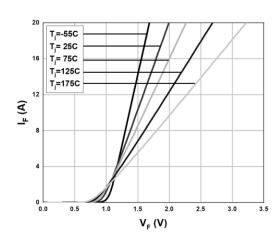
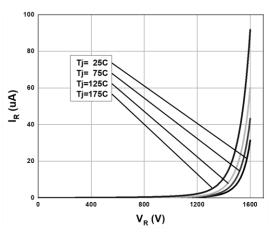


Fig. 1 Forward Characteristics





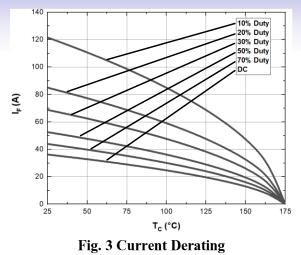
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Typical Performance



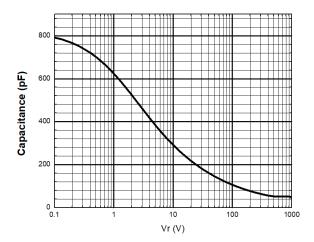


Fig. 5 Capacitance vs. Reverse Voltage

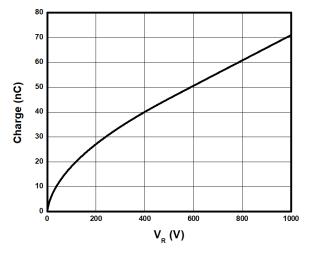
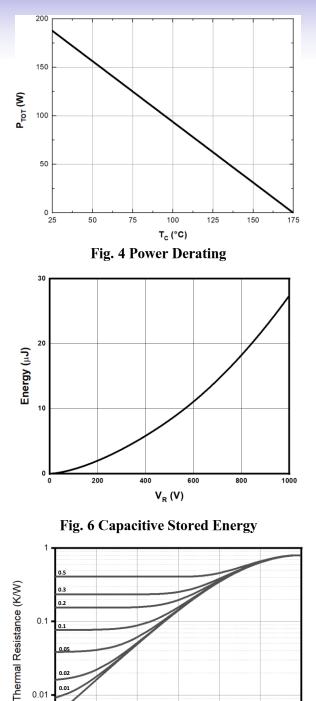


Fig. 7 Total Charge vs. Reverse Voltage





1m

10m

. 100µ

0.01

ingle Puls

10µ

1μ

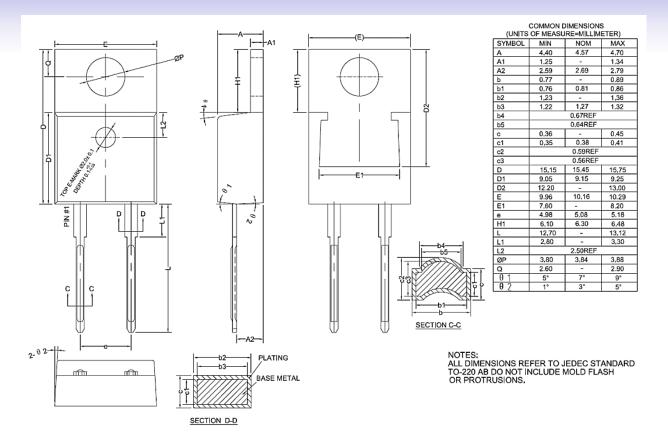
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100m



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Package TO-220-2L (Unit: mm)



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